

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05039A		1 of 1

TYPE : 6PT1803N3T**

CHIP SIZE	0.80 * 0.80 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	23,580 pcs

Maximum Ratings(Ta=25°C)

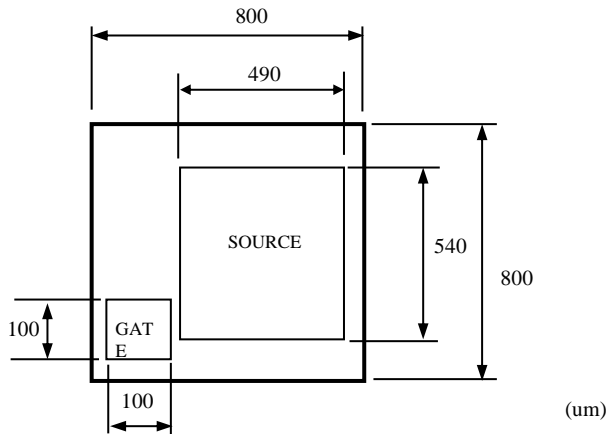
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	2	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±5	uA	VGS=±20V VDS=0V
2	IDSS			500	nA	VDS=30V VGS=0V
3	BVDSS	33			V	ID=250uA
4	VGS(off)	1.1		2.3	V	ID=250uA
5	Ron 1		0.05	0.08	Ω	ID=0.95A VGS=10V
6	Ron 2		0.08	0.11	Ω	ID=0.95A VGS=4.5V
7	VSD			0.9	V	IS=1A

※ Built-in ZD between Gate and Source. ESD Protected : 2000V



TENTATIVE

NOTE: